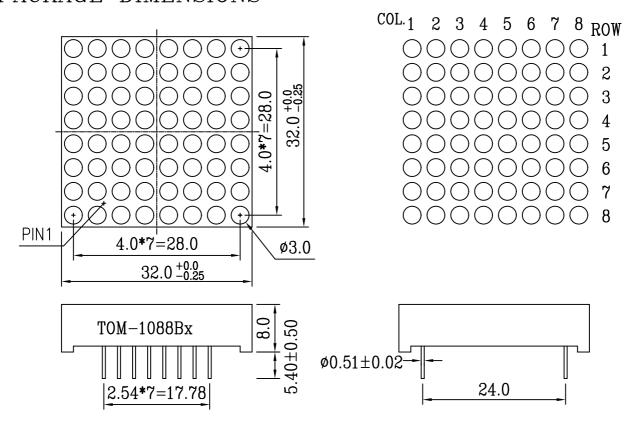


TAIWAN OASIS LED DATA SHEET

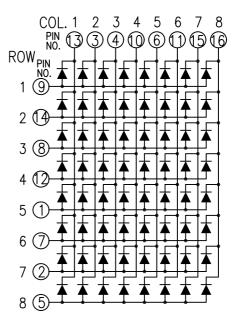
PART NO.: TOM-1088BMR-B

	APPEARANC	Œ	TECHNOLOGY	AlGaInP/GaAs		
EAGE	CECMENT	PIN	SOURCE COLOR	Ultra-red		
FACE	SEGMENT		DRIVER MODE	Row. Anode		
Black	Black White 00.51x10.28		PACKING	Styrene Foam		

PACKAGE DIMENSIONS



INTERNAL CIRCUIT DIAGRAM



DATE	08/15/01	SCALE	1.5:1	TOLERANCE	±0.25 ANGLE ±1°	DRAWN	H.X.K	CHECKED	
UNIT	M/M	SHEET NO.	1/2	DRAWING NO.	S-1088BMR-B-A	CUSTOMER		APPROVED	

PART NO.: TOM-1088BMR-B

ABSOLUTE MAXIMUM RATINGS AT TA=25°C

PARAMETER	VALUE	UNITS	
Power Dissipation Per Dot	60	mW	
Peak Forward Current Per Dot (1/10 Duty Cycle, 0.1ms Pulse Width)	70	mA	
Continuous Forward Current Per Dot	18	mA	
Recommend Operating Current	12	mA	
Reverse Voltage Per Dot	5	V	
Operating Temperature Range	-25 to +85	°C	
Storage Temperature Range	-30 to +85	°C	
Lead Solder Temperature(1/10 Inch Below Seating Plane)	260°C for 3 sec.		

ELECTRICAL/OPTICAL CHARACTERISTICS AT TA=25°C

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITION	GRADE
Luminous Intensity Per Dot	Iv	7988	9185	10383	ucd	$I_F = 10 \text{mA}$	N
Luminous Intensity Per Dot	Iv	10384	11941	13499	ucd	$I_F = 10 \text{mA}$	Р
Luminous Intensity Per Dot	Iv	13500	15524	17549	ucd	$I_F = 10 \text{mA}$	R
Peak Emission Wavelength	λр		645		nm	I _F =20mA	
Spectral Line Half-Width	Δλ		22		nm	I _F =20mA	
Forward Voltage Per Dot	VF	1.8	2.0	2.4	V	I _F =20mA	
Reverse Current Per Dot	IR			100	μA	Vr =5V	
Luminous Intensity Matching Rate	Iv-m			2.0:1		$I_F = 20 \text{mA}$	

DATE	08/15/0'1	SCALE		TOLERANCE		DRAWN	H.X.K	CHECKED	
UNIT		SHEET NO.	2/2	DRAWING NO.	S-1088BMR-B-A	CUSTOMER		APPROVED	